(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
8 January 2009 (08.01.2009)

PCT

(10) International Publication Number
WO 2009/005787 A1

(51) International Patent Classification:
H01L 21/265 (2006.01) *H01L 21/336* (2006.01)
H01L 21/266 (2006.01) *H01L 21/8238* (2006.01)

(21) International Application Number:
PCT/US2008/008152

(22) International Filing Date: 30 June 2008 (30.06.2008)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
102007030056.7 29 June 2007 (29.06.2007) DE
12/026,273 5 February 2008 (05.02.2008) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

(54) Title: BLOCKING PRE-AMORPHIZATION OF A GATE ELECTRODE OF A TRANSISTOR

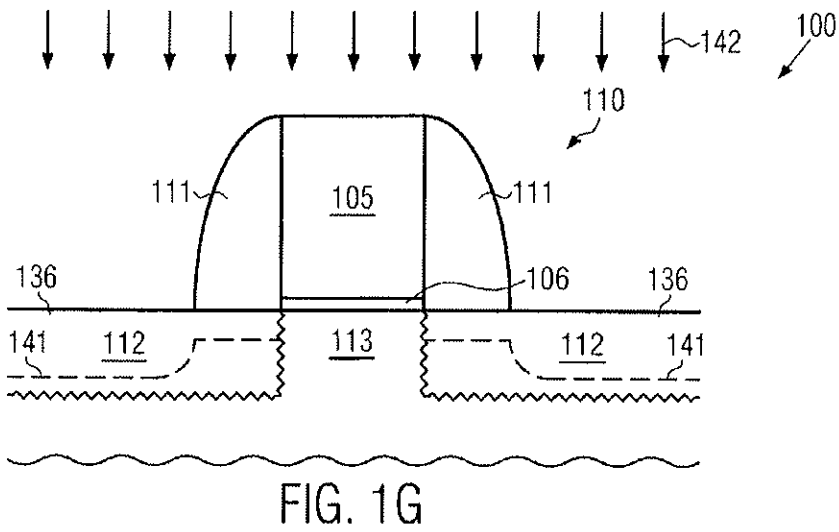


FIG. 1G

(57) Abstract: A technique is presented which provides for a selective pre-amorphization of source/drain regions of a transistor while preventing pre-amorphization of a gate electrode of the transistor. Illustrative embodiments include the formation of a pre-amorphization implant blocking material over the gate electrode. Further illustrative embodiments include inducing a strain in a channel region by use of various stressors.

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